

Application Number: 10/765,346 (Peng et al.) Art Unit 2815 Amendment continued 3 of 5

CLAIMS: Please amend the claims according to the status designations in the following list, which contains all claims that were ever in the patent application, with the text of all active claims.

What I claim are:

1. (withdraw).
2. (withdraw).
3. (withdraw).
4. (withdraw).
5. (withdraw).
6. (withdraw).
7. (withdraw).
8. (withdraw).
9. (withdraw).
10. (withdraw).
11. (withdraw).
12. (withdraw).
13. (withdraw).
14. (Currently amended) A vertical semiconductor chip or device comprising
 - a) an electrically conductive submount chip;
 - b) an epitaxial layer comprising a second confinement layer, an active layer, and a first confinement layer stacked on said submount chip;

Application Number: 10/765,346 (Peng et al.) Art Unit 2813 Amendment continued 4 of 5

- c) reflective and Ohmic contact layers sandwiched between said epitaxial layer and said submount chip;
- d) a patterned contact pad disposed on said first confinement layer wherein said patterned contact pad comprising at least one wire bonding pad.
- 15. (withdraw).
- 16. (Currently amended) The vertical semiconductor chip or device of claim 14 further comprising a current spreading layer sandwiched between said patterned contact pad and said first confinement layer.
- 17. (withdraw)
- 18. (Currently amended) The vertical semiconductor chip or device of claim 14 wherein said patterned contact pad is a grid-ring-shaped contact pad with at least one wire bonding pad.
- 19. (withdraw).
- 20. (withdraw).
- 21. (withdraw).
- 22. (withdraw).
- 23. (withdraw).
- 24. (withdraw).